Hex Inverting Schmitt Triggers

UT54ACS14E/UT54ACTS14E

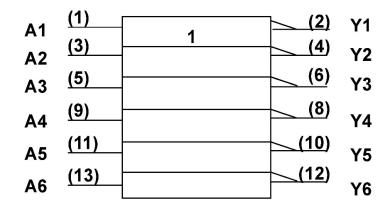
Features

- 0.6µm CRH CMOS Process
 - Latchup immune
- · High speed
- Low power consumption
- Wide power supply operating range of 3.0V to 5.5V
- Available QML Q or V processes
- 14-lead flatpack
- UT54ACS14E SMD 5962-96524
- UT54ACTS14E SMD 5962-96525

Function Table

Input A	Output Y
Н	L
L	Н

Logic Symbol



Note:

1) Logic symbol in accordance with ANSI/IEEE standard 91-1984 and IEC Publication 617-12.

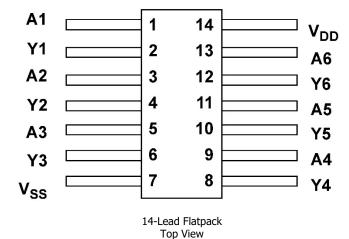
Description

The UT54ACS14E and the UT54ACTS14E are hex inverters with schmitt trigger inputs. The circuits perform the Boolean function $Y = \overline{A}$.

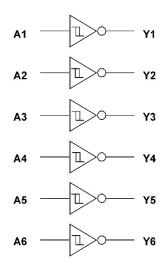
The devices are characterized over full HiRel temperature range of -55°C to +125°C.



Pinouts



Logic Diagram



Operational Environment ¹

Parameter	Limit	Units
Total Dose	1.0E6	rads(Si)
SEU Threshold ²	80	MeV-cm ² /mg
SEL Threshold	108	MeV-cm ² /mg
Neutron Fluence	1.0E14	n/cm²

- 1) Logic will not latchup during radiation exposure within the limits defined in the table.
- 2) Device storage elements are immune to SEU affects.



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Absolute Maximum Ratings

Symbol	Parameter	Limit	Units
V_{DD}	Supply voltage	-0.3 to 7.0	٧
V _{I/O}	Voltage any pin	-0.3 to $V_{DD} + 0.3$	V
T _{STG}	Storage Temperature range	-65 to +150	°C
Tı	Maximum junction temperature	+175	°C
T _{LS}	Lead temperature (soldering 5 seconds)	+300	°C
Θ _{JC}	Thermal resistance junction to case	15 (ACS) 15.5 (ACTS)	°C/W
$\mathbf{I}_{\mathbf{I}}$	DC input current	±10	mA
P _D	Maximum package power dissipation permitted @ Tc= +125°C	3.3	W

Note:

- 1) Stresses outside the listed absolute maximum ratings may cause permanent damage to the device. This is a stress rating only, functional operation of the device at these or any other conditions beyond limits indicated in the operational sections is not recommended. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.
- 2) Per MIL-STD-883, method 1012.1, Section 3.4.1, $P_D = (T_{j(max)} T_{c(max)}) / \Theta_{jc}$

Recommended Operating Conditions

Symbol	Parameter	Limit	Units
V_{DD}	Supply voltage	3.0 to 5.5	V
V_{IN}	Input voltage any pin	0 to V _{DD}	V
T _C	Temperature range	-55 to +125	°C



DC Electrical Characteristics for the UT54ACS14E 7

 $(V_{DD} = 3.0V \text{ to } 5.5V; V_{SS} = 0V^6; -55^{\circ}C < T_C < +125^{\circ}C)$

Symbol	Description	1	Condition	MIN	MAX	Units
V_{T+}	Schmitt trigg going thresh		V _{DD} from 3.0V to 5.5V		0.7V _{DD}	V
V _T -	Schmitt trigg	ger negative- nold ¹	V _{DD} from 3.0V to 5.5V	0.3V _{DD}		V
V _{H1}	Range of hy	steresis (V _{T+} - V _{T-})	V _{DD} from 4.5V to 5.5V	0.6	1.5	V
V _{H2}	Range of hy	steresis (V _{T+} - V _{T-})	V _{DD} from 3.0V to 3.6V	0.3	1.2	V
I_{IN}	Input leakag	ge current	$V_{IN} = V_{DD}$ or V_{SS}	-1	1	μΑ
V _{OL}	Low-level ou	utput voltage ³	$I_{OL} = 100 \mu A$ V_{DD} from 3.0V to 5.5V		0.25	V
V _{OH}	High-level o	utput voltage ³	$I_{OH} = -100\mu A$ V_{DD} from 3.0V to 5.5V	V _{DD} - 0.25		V
I_{OS1}	Short-circuit	output current ^{2, 4}	$V_O = V_{DD}$ and V_{SS} V_{DD} from 4.5V to 5.5V	-200	200	mA
I_{OS2}	Short-circuit	output current ^{2, 4}	$V_O = V_{DD}$ and V_{SS} V_{DD} from 3.0V to 3.6V	-100	100	mA
I_{OL1}	Low level output current ⁹ (sink)		$V_{IN} = V_{DD}$ or V_{SS} $V_{OL} = 0.4V$ V_{DD} from 4.5V to 5.5V	8		mA
I _{OL2}	Low level output current ⁹ (sink)		$V_{IN} = V_{DD}$ or V_{SS} $V_{OL} = 0.4V$ V_{DD} from 3.0V to 3.6V	6		mA
$ m I_{OH1}$	High level output current ⁹ (source)		$V_{IN} = V_{DD}$ or V_{SS} $V_{OH} = V_{DD} - 0.4V$ V_{DD} from 4.5V to 5.5V	-8		mA
$ m I_{OH2}$	High level o (source)	utput current ⁹	$V_{IN} = V_{DD}$ or V_{SS} $V_{OH} = V_{DD}$ - 0.4V V_{DD} from 3.0V to 3.6V	-6		mA
P _{total1}	Power dissip	pation ^{2, 8}	$C_L = 50pF$ V_{DD} from 4.5V to 5.5V		1.8	mW/ MHz
P _{total2}	Power dissipation ^{2, 8}		$C_L = 50 pF$ V_{DD} from 3.0V to 3.6V		0.72	mW/ MHz
	Pre-Rad All Device Types			10		
I _{DDO} Suppl	Quiescent Supply Current	Dovice Type 07	$V_{IN} = V_{DD} \text{ or } V_{SS}$ $V_{DD} = V_{DD} \text{ MAX}$		50	μΑ
		Post-Rad Device Type - 02			130	
C _{IN}	Input capacitance 5		$f = 1$ MHz, $V_{DD} = 0$		15	pF
C _{OUT}	Output capa	citance ⁵	$f = 1$ MHz, $V_{DD} = 0$		15	pF



Notes:

- 1) Functional tests are conducted in accordance with MIL-STD-883 with the following input test conditions: $V_{IH} = V_{IH}(min) + 20\%$, 0%; $V_{IL} = V_{IL}(max) + 0\%$, 50%, as specified herein, for TTL, CMOS, or Schmitt compatible inputs. Devices may be tested using any input voltage within the above specified range, but are guaranteed to $V_{IH}(min)$ and $V_{IL}(max)$.
- 2) Supplied as a design limit but not guaranteed or tested.
- 3) Per MIL-PRF-38535, for current density ≤5.0E5 amps/cm², the maximum product of load capacitance (per output buffer) times frequency should not exceed 3,765pF/MHz.
- 4) Not more than one output may be shorted at a time for maximum duration of one second.
- 5) Capacitance measured for initial qualification and when design changes may affect the value. Capacitance is measured between the designated terminal and Vss at frequency of 1MHz and a signal amplitude of 50mV rms maximum.
- 6) Maximum allowable relative shift equals 50mV.
- 7) Device type 02 is only offered with a TID tolerance guarantee of 3E5 rads(Si), and 1E6 rads(Si), and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A and section 3.11.2. Device type 03 is only offered with a TID tolerance guarantee of 1E5 rads(Si), 3E5 rads(Si), and 5E5 rads(Si), and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A.
- 8) Power dissipation specified per switching output.
- 9) Guaranteed by characterization, but not tested.

AC Electrical Characteristics for the UT54ACS14E²

 $(V_{DD} = 3.0V \text{ to } 5.5V; V_{SS} = 0V^{-1}, -55^{\circ}C < T_{C} < +125^{\circ}C)$

Symbol	Parameter	Condition	$V_{ extsf{DD}}$	Minimum	Maximum	Unit
			3.0V to 3.6V	2	18	ns
t_{PHL}	Input to Yn	$C_L = 50pF$	4.5V to 5.5V	2	14	ns
			3.0V to 3.6V	2	17	ns
t_{PLH}	Input to Yn	$C_L = 50pF$	4.5V to 5.5V	2	13	ns
			3.0V to 3.6V	2	14	ns
t_{PHL}	Input to Yn	$C_L = 30pF$	4.5V to 5.5V	2	10	ns
			3.0V to 3.6V	2	13	ns
t_{PLH}	Input to Yn	$C_L = 30pF$	4.5V to 5.5V	2	9	ns

- 1) Maximum allowable relative shift equals 50mV.
- 2) Device type 02 is only offered with a TID tolerance guarantee of 3E5 rads(Si), and 1E6 rads(Si), and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A and section 3.11.2. Device type 03 is only offered with a TID tolerance guarantee of 1E5 rads(Si), 3E5 rads(Si), and 5E5 rads(Si), and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A.



DC Electrical Characteristics for the UT54ACTS14E 7

 $(V_{DD} = 3.0V \text{ to } 5.5V; V_{SS} = 0V^6; -55^{\circ}C < T_C < +125^{\circ}C)$

Symbol	Description		Condition	MIN	MAX	Unit
V _{T+1}	Schmitt trigge threshold ¹	r positive-going	V _{DD} from 4.5V to 5.5V		2.25	V
V _{T+2}	Schmitt trigge threshold ¹	r positive-going	V _{DD} from 3.0V to 3.6V		2.0	V
V _{T-1}	Schmitt trigge threshold ¹	r negative-going	V _{DD} from 4.5V to 5.5V	0.5		V
V _{T-2}	Schmitt trigge threshold ¹	r negative-going	V _{DD} from 3.0V to 3.6V	0.5		V
V _{H1}	Range of hyst	eresis (V _{T+1} - V _{T-1})	V _{DD} from 4.5V to 5.0V	0.4	1.5	V
V _{H2}	Range of hyst	eresis (V _{T+2} - V _{T-2})	V _{DD} from 3.0V to 3.6V	0.2	1.2	V
${ m I_{IN}}$	Input leakage	current	$V_{IN} = V_{DD}$ or V_{SS}	-1	1	μΑ
V _{OL1}	Low-level outp	out voltage ³	$I_{OL} = 8mA$ V _{DD} from 4.5V to 5.5V		0.4	V
V _{OL2}	Low-level outp	out voltage ³	$I_{OL} = 6mA$ V _{DD} from 3.0V to 3.6V		0.4	V
V _{OH1}	High-level out	put voltage ³	$I_{OH} = -8mA$ V_{DD} from 4.5V to 5.5V	0.7V _{DD}		V
V _{OH2}	High-level output voltage ³		$I_{OH} = -6mA$ V_{DD} from 3.0V to 3.6V	2.4		V
I _{OS1}	Short-circuit output current ^{2, 4}		$V_O = V_{DD}$ or V_{SS} V_{DD} from 4.5V to 5.5V	-200	200	mA
I _{OS1}	Short-circuit output current ^{2, 4}		$V_O = V_{DD}$ or V_{SS} V_{DD} from 3.0V to 3.6V	-100	100	mA
I _{OL1}	Low level output current ⁹		$V_{IN} = V_{DD}$ or V_{SS} $V_{OL} = 0.4V$ V_{DD} from 4.5V to 5.5V	8		mA
I _{OL2}	Low level output current ⁹		$V_{IN} = V_{DD}$ or V_{SS} $V_{OL} = 0.4V$ V_{DD} from 3.0V to 3.6V	6		mA
І _{ОН1}	High level output current ⁹		$V_{IN} = V_{DD}$ or V_{SS} $V_{OH} = V_{DD}$ -0.4V, V_{DD} from 4.5V to 5.5V	-8		mA
I _{OH2}	High level output current ⁹		$V_{IN} = V_{DD}$ or V_{SS} $V_{OH} = V_{DD} - 0.4V$ V_{DD} from 3.0V to 3.6V	-6		mA
P _{total1}	Power dissipation ^{2, 8}		$C_L = 50pF$ V_{DD} from 4.5V to 5.5V		1.3	mW/ MHz
P _{total2}	Power dissipation ^{2, 8}		$C_L = 50pF$ V_{DD} from 3.0V to 3.6V		0.5	mW/ MHz
		Pre-Rad All Device Types			10	
${ m I}_{ m DDQ}$	I _{DDQ} Quiescent Supply Current	Post-Rad Device Type - 03	$V_{IN} = V_{DD} \text{ or } V_{SS}$ $V_{DD} = V_{DD} \text{ MAX}$		50	μΑ
		Post-Rad Device Type - 02			130	



Symbol	Description	Condition	MAX	MIN	Unit
ΔI_{DDQ}	Quiescent Supply Current Delta	For input under test			
		$V_{IN} = V_{DD}$ -2.1V			
		For all other inputs		3.1	mA
		$V_{IN} = V_{DD}$ or V_{SS}			
		$V_{DD} = 5.5V$			
C _{IN}	Input capacitance 5	$f = 1$ MHz, $V_{DD} = 0$		15	pF
Cout	Output capacitance ⁵	$f = 1$ MHz, $V_{DD} = 0$		15	pF

Notes:

- 1) Functional tests are conducted in accordance with MIL-STD-883 with the following input test conditions: $V_{IH} = V_{IH}(min) + 20\%$, 0%; $V_{IL} = V_{IL}(max) + 0\%$, 50%, as specified herein, for TTL, CMOS, or Schmitt compatible inputs. Devices may be tested using any input voltage within the above specified range, but are guaranteed to $V_{IH}(min)$ and $V_{IL}(max)$.
- 2) Supplied as a design limit but not guaranteed or tested.
- 3) Per MIL-PRF-38535, for current density ≤5.0E5 amps/cm², the maximum product of load capacitance (per output buffer) times frequency should not exceed 3,765pF/MHz.
- 4) Not more than one output may be shorted at a time for maximum duration of one second.
- 5) Capacitance measured for initial qualification and when design changes may affect the value. Capacitance is measured between the designated terminal and Vss at frequency of 1MHz and a signal amplitude of 50mV rms maximum.
- 6) Maximum allowable relative shift equals 50mV.
- 7) Device type 02 is only offered with a TID tolerance guarantee of 3E5 rads(Si), and 1E6 rads(Si), and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A and section 3.11.2. Device type 03 is only offered with a TID tolerance guarantee of 1E5 rads(Si), 3E5 rads(Si), and 5E5 rads(Si), and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A.
- 8) Power dissipation specified per switching output.
- 9) Guaranteed by characterization, but not tested.

AC Electrical Characteristics for the UT54ACTS14E ²

 $(V_{DD} = 3.0V \text{ to } 5.5V; V_{SS} = 0V^{-1}, -55^{\circ}C < T_{C} < +125^{\circ}C)$

Symbol	Parameter	Condition	$V_{ extsf{DD}}$	Minimum	Maximum	Unit
			3.0V to 3.6V	2	20	nc
t_{PHL}	Input to Yn	$C_L = 50pF$	4.5V to 5.5V	2	9	ns
			3.0V to 3.6V	3	20	nc
t_{PLH}	Input to Yn	$C_L = 50pF$	4.5V to 5.5V	2	12	ns

- 1) Maximum allowable relative shift equals 50mV.
- 2) Device type 02 is only offered with a TID tolerance guarantee of 3E5 rads(Si), and 1E6 rads(Si), and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A and section 3.11.2. Device type 03 is only offered with a TID tolerance guarantee of 1E5 rads(Si), 3E5 rads(Si), and 5E5 rads(Si), and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A.



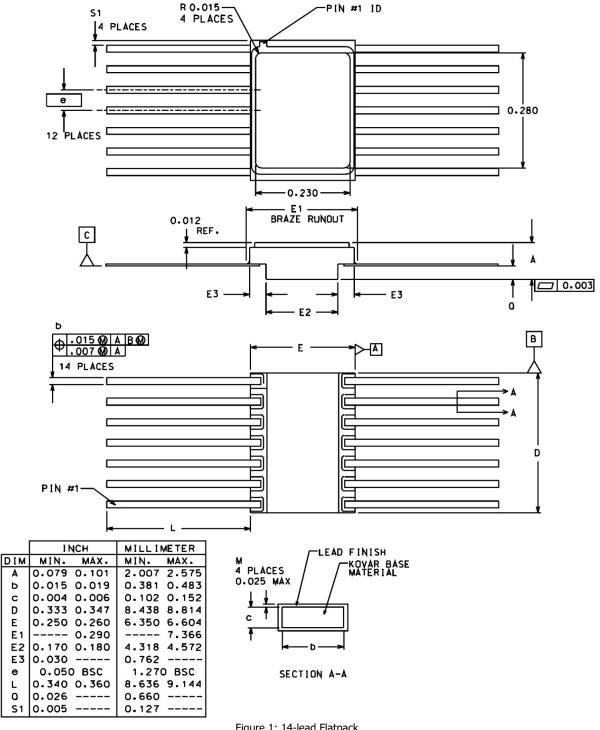
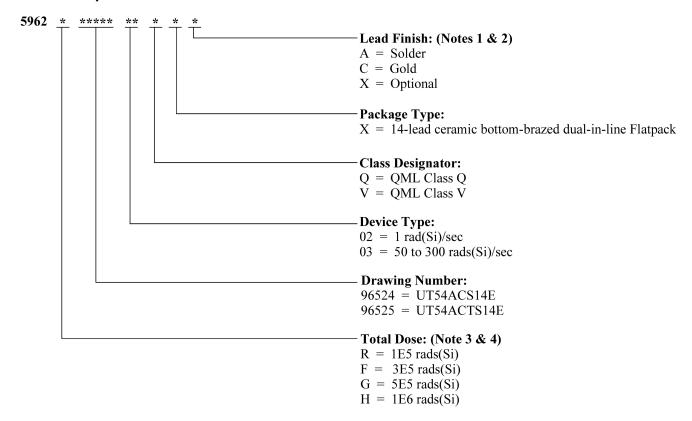


Figure 1: 14-lead Flatpack

- 1) All exposed metallized areas are gold plated over electroplated nickel per MIL-PRF-38535.
- 2) The lid is electrically connected to V_{SS} .
- 3) Lead finishes are in accordance with MIL-PRF-38535.
- 4) Dimension symbol is in accordance with MIL-PRF-38533.
- 5) Lead position and colanarity are not measured.



UT54ACS14E/UT54ACTS14E: SMD



- 1) Lead finish (A,C, or X) must be specified.
- 2) If an "X" is specified when ordering, part marking will match the lead finish and will be either "A" (solder) or "C" (gold).
- 3) Total dose radiation must be specified when ordering. QML-2 and V is not available without radiation testing. For prototyping inquiries, contact factory.
- 4) Device type 02 is only offered with a TID tolerance guarantee of 3E5 rads(Si) or 1E6 rads(Si) and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A and section 3.11.2. Device type 03 is only offered with a TID tolerance guarantee of 1E5 rads(Si), 3E5 rads(Si), and 5E5 rads(Si), and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A.

Revision Date	Description of Change	Author
10-17	Page 4 edited PTOTAL2 Pages 4 and 6 edited IDDQ Page 5 AC Electricals Added new CAES Data Sheet template to the document.	RT
1-18	Updates to reflect current SMD	RT



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UT54ACS14E/UT54ACTS14E

Datasheet Definitions

	DEFINITION			
Advanced Datasheet	CAES reserves the right to make changes to any products and services described herein at any time without notice. The product is still in the development stage and the datasheet is subject to change. Specifications can be TBD and the part package and pinout are not final.			
Preliminary Datasheet	CAES reserves the right to make changes to any products and services described herein at any time without notice. The product is in the characterization stage and prototypes are available.			
Datasheet	Product is in production and any changes to the product and services described herein will follow a formal customer notification process for form, fit or function changes.			

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